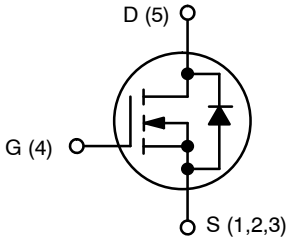
MOSFET - Power, Single N-Channel, STD Gate, SO8-FL

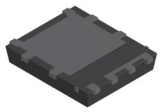
40 V, 0.52 mΩ, 414 A

NVMFWS0D5N04XM

$V_{(BR)DSS}$	$R_{DS(on)}$ MAX	I_D MAX
40 V	0.52 mΩ @ 10 V	414 A



N−CHANNEL MOSFET



DFNW5 (SO−8FL WF)
CASE 507BD

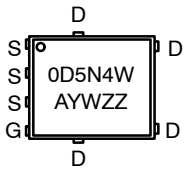
Features

- Low $R_{DS(on)}$ to Minimize Conduction Losses
- Low Capacitance to Minimize Driver Losses
- Small Footprint (5 x 6 mm) with Compact Design
- AEC−Q101 Qualified and PPAP Capable
- These Devices are Pb−Free, Halogen Free/BFR Free and are RoHS Compliant

Applications

- Motor Drive
- Battery Protection
- Synchronous Rectification

MARKING DIAGRAM



A = Assembly Location
Y = Year
W = Work Week
ZZ = Lot Traceabililty

ORDERING INFORMATION

See detailed ordering, marking and shipping information in the package dimensions section on page 5 of this data sheet.

MAXIMUM RATINGS (T_J = 25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain−to−Source Voltage		V_{DSS}	40	V
Gate−to−Source Voltage		V_{GS}	±20	V
Continuous Drain Current	T_C = 25°C	I_D	414	A
	T_C = 100°C		293	
Power Dissipation	T_C = 25°C	P_D	163	W
Pulsed Drain Current	T_C = 25°C, t_p = 10 μs	I_{DM}	900	A
Pulsed Source Current (Body Diode)		I_{SM}	900	
Operating Junction and Storage Temperature Range		T_J, T_{STG}	−55 to +175	°C
Source Current (Body Diode)		I_S	251	A
Single Pulse Avalanche Energy	I_{PK} = 28.2 A	E_{AS}	1434	mJ
Lead Temperature for Soldering Purposes (1/8″ from case for 10 s)		T_L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

THERMAL CHARACTERISTICS

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction−to−Case (Note 2)	$R_{\theta JC}$	0.92	°C/W
Thermal Resistance, Junction−to−Ambient (Notes 1, 2)	$R_{\theta JA}$	38.9	

1. Surface−mounted on FR4 board using 650 mm^2 pad, 2 oz Cu pad.
2. The entire application environment impacts the thermal resistance values shown, they are not constants and are only valid for the particular conditions noted.

ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
OFF CHARACTERISTICS						
Drain−to−Source Breakdown Voltage	$V_{(BR)DSS}$	V_{GS} = 0 V, I_D = 1 mA, T_J = 25°C	40			V
Drain−to−Source Breakdown Voltage Temperature Coefficient	$\Delta V_{(BR)DSS}/\Delta T_J$	I_D = 1 mA, Referenced to 25°C		15		mV/°C
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS} = 40 V, T_J = 25°C			1	μA
		V_{DS} = 40 V, T_J = 125°C			60	
Gate−to−Source Leakage Current	I_{GSS}	V_{GS} = 20 V, V_{DS} = 0 V			100	nA
ON CHARACTERISTICS						
Drain−to−Source On Resistance	$R_{DS(on)}$	V_{GS} = 10 V, I_D = 50 A, T_J = 25°C		0.43	0.52	mΩ
Gate Threshold Voltage	$V_{GS(TH)}$	V_{GS} = V_{DS}, I_D = 240 μA, T_J = 25°C	2.5	3.0	3.5	V
Gate Threshold Voltage Temperature Coefficient	$\Delta V_{GS(TH)}/\Delta T_J$	V_{GS} = V_{DS}, I_D = 240 μA		−7.21		mV/°C
Forward Trans−conductance	g_{FS}	V_{DS} = 5 V, I_D = 50 A		267		S
CHARGES, CAPACITANCES & GATE RESISTANCE						
Input Capacitance	C_{ISS}	V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz		6232		pF
Output Capacitance	C_{OSS}			3987		
Reverse Transfer Capacitance	C_{RSS}			53.9		
Total Gate Charge	$Q_{G(TOT)}$	V_{DD} = 32 V, I_D = 50 A, V_{GS} = 6 V		60.5		nC
Total Gate Charge	$Q_{G(TOT)}$	V_{DD} = 32 V, I_D = 50 A, V_{GS} = 10 V		97.9		
Threshold Gate Charge	$Q_{G(TH)}$			18.2		
Gate−to−Source Charge	Q_{GS}			27.4		
Gate−to−Drain Charge	Q_{GD}			18.5		
Gate Resistance	R_G	f = 1 MHz		0.47		Ω
SWITCHING CHARACTERISTICS						
Turn−On Delay Time	$t_{d(ON)}$	Resistive Load, V_{GS} = 0/10 V, V_{DD} = 32 V, I_D = 50 A, R_G = 0 Ω		8.64		ns
Rise Time	t_r			7.02		
Turn−Off Delay Time	$t_{d(OFF)}$			13.7		
Fall Time	t_f			6.85		
SOURCE−TO−DRAIN DIODE CHARACTERISTICS						
Forward Diode Voltage	V_{SD}	I_S = 50 A, V_{GS} = 0 V, T_J = 25°C		0.8	1.2	V
		I_S = 50 A, V_{GS} = 0 V, T_J = 125°C		0.65		
Reverse Recovery Time	t_{RR}	V_{GS} = 0 V, I_S = 50 A, dI/dt = 100 A/μs, V_{DD} = 32 V		101		ns
Charge Time	t_a			56.9		
Discharge Time	t_b			44.8		
Reverse Recovery Charge	Q_{RR}			286		nC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

TYPICAL CHARACTERISTICS

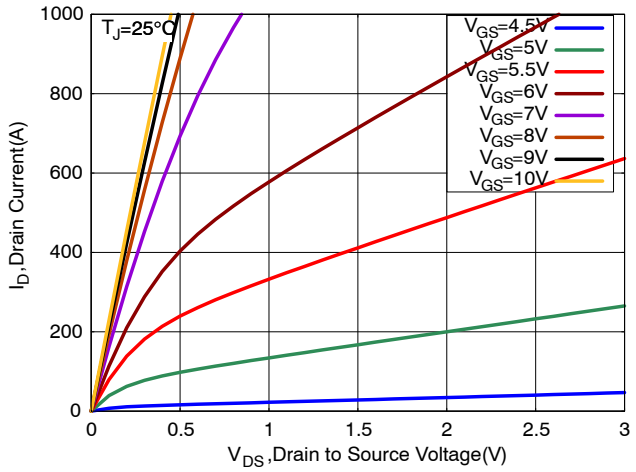


Figure 1. On−Region Characteristics

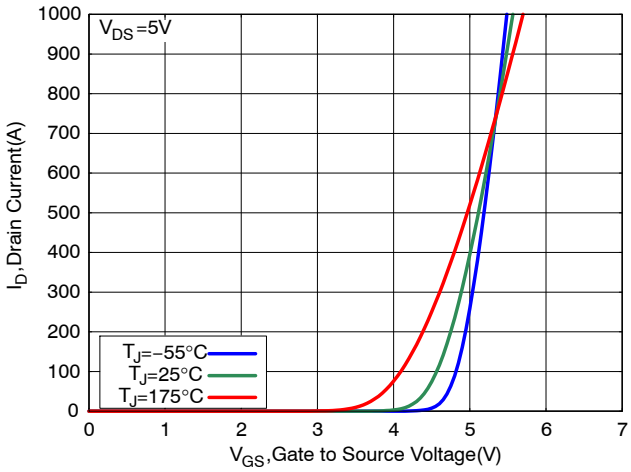


Figure 2. Transfer Characteristics

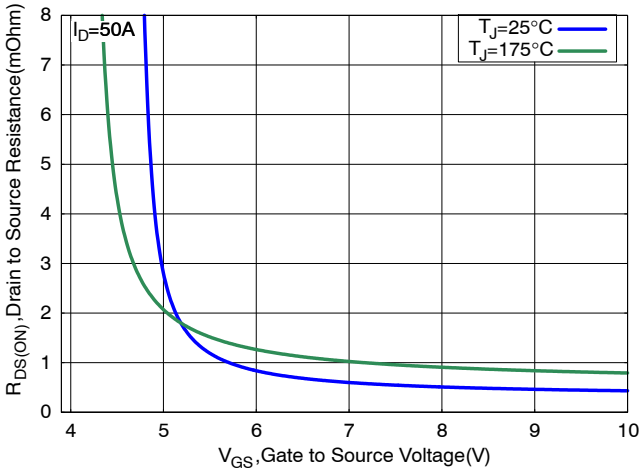


Figure 3. On−Resistance vs. Gate Voltage

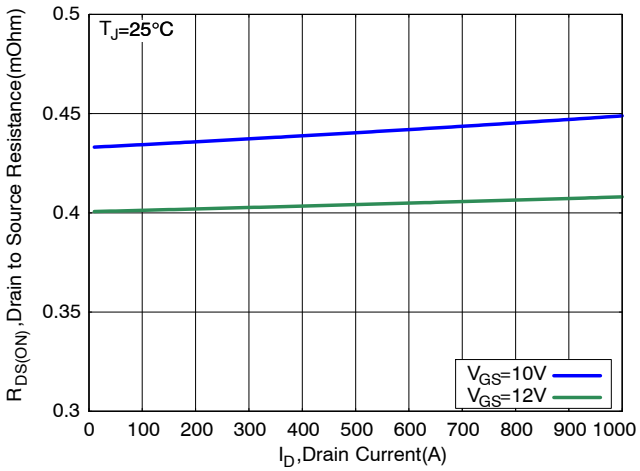


Figure 4. On−Resistance vs. Drain Current

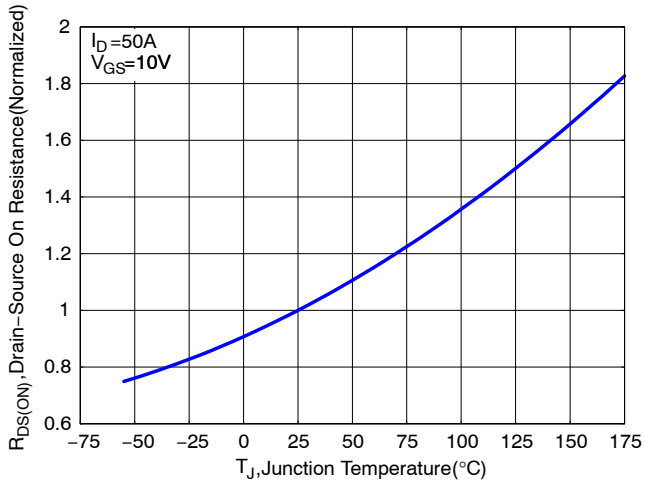


Figure 5. Normalized ON Resistance vs. Junction Temperature

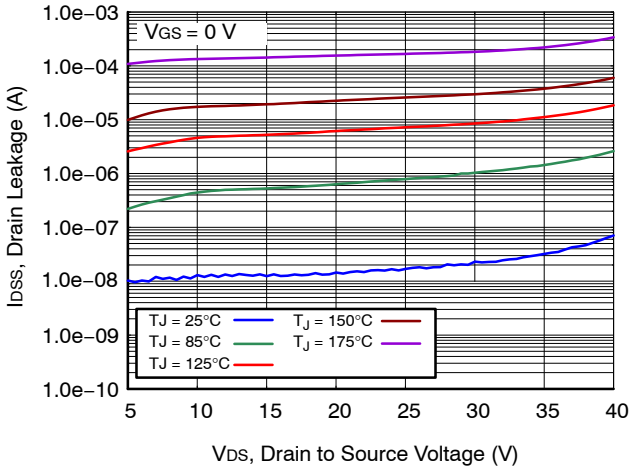


Figure 6. Drain Leakage vs. Drain to Source Voltage

TYPICAL CHARACTERISTICS (continued)

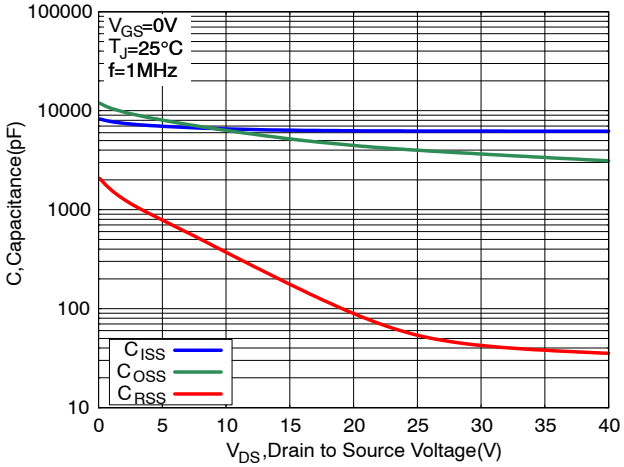


Figure 7. Capacitance Characteristics

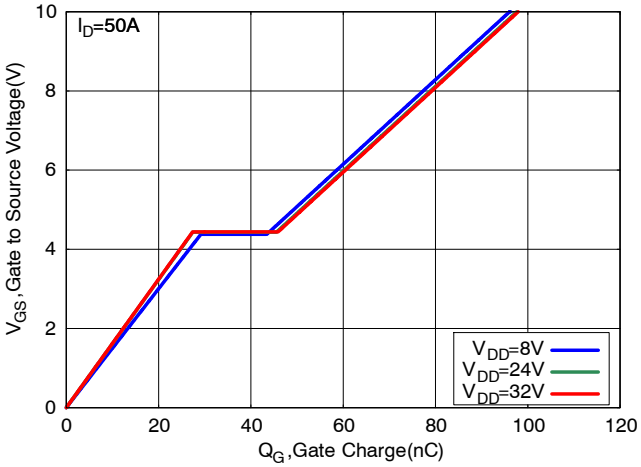


Figure 8. Gate Charge Characteristics

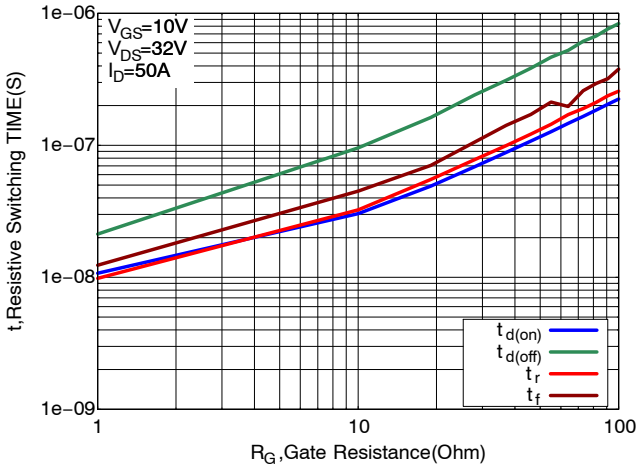


Figure 9. Resistive Switching Time Variation vs. Gate Resistance

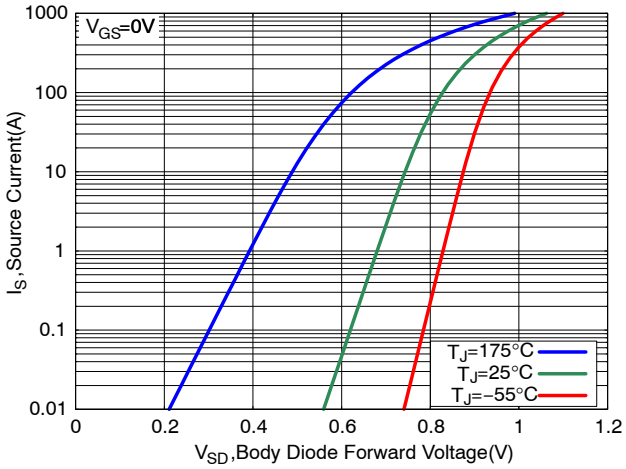


Figure 10. Diode Forward Characteristics

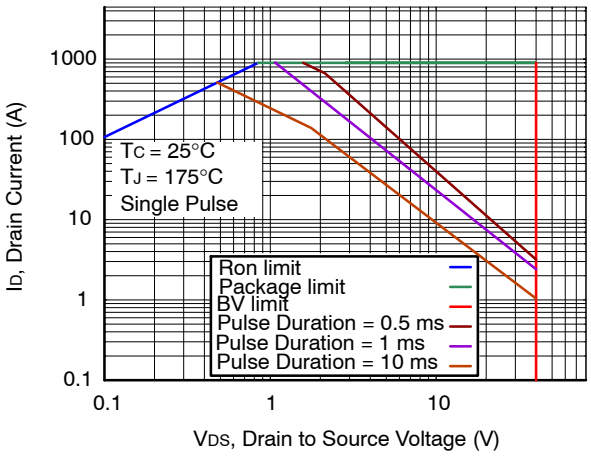


Figure 11. Maximum Rated Forward Biased Safe Operating Area

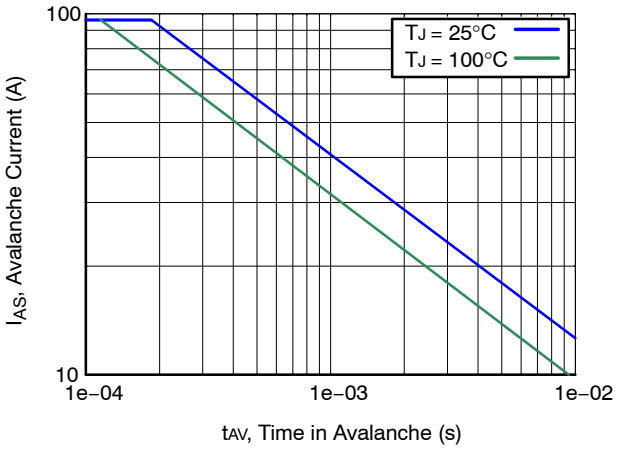


Figure 12. Ipeak vs. Time in Avalanche

TYPICAL CHARACTERISTICS (continued)

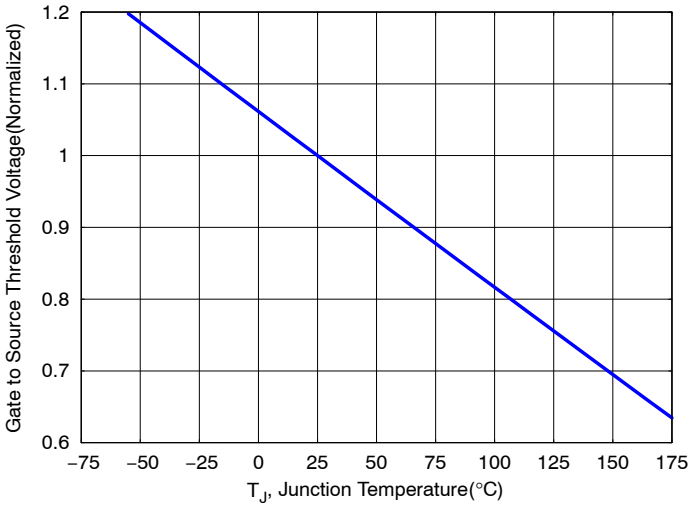


Figure 13. Gate Threshold Voltage vs. Junction Temperature

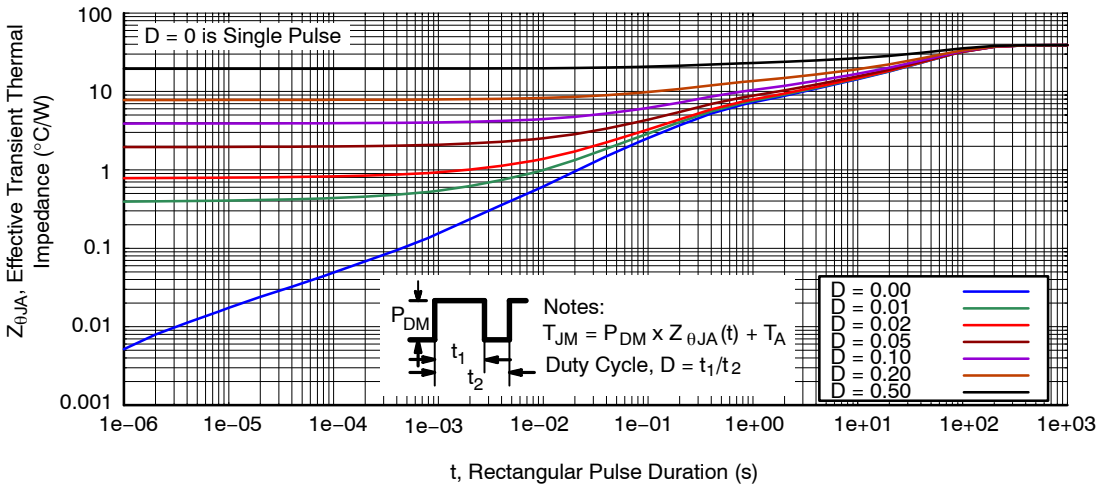
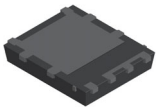


Figure 14. Thermal Characteristics

DEVICE ORDERING INFORMATION

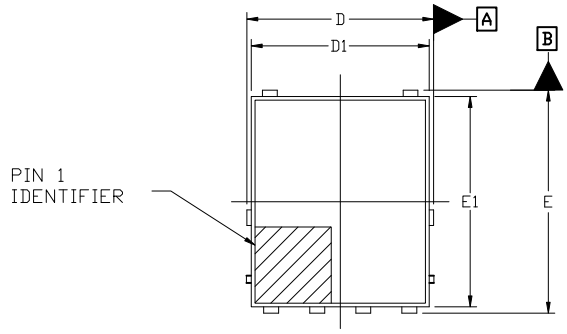
Device	Marking	Package	Shipping†
NVMFWS0D5N04XMT1G	0D5N4W	DFNW5 (Pb−Free)	1500 / Tape & Reel

†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

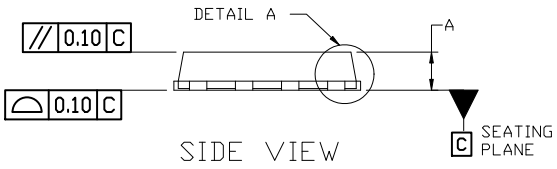


DFNW5 5x6, FULL−CUT SO8FL WF
CASE 507BD
ISSUE O

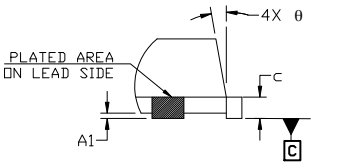
DATE 13 APR 2021



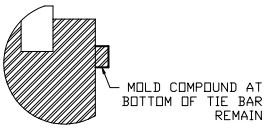
TOP VIEW



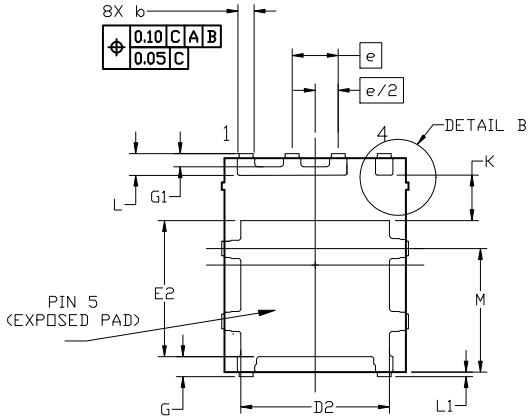
SIDE VIEW



DETAIL A



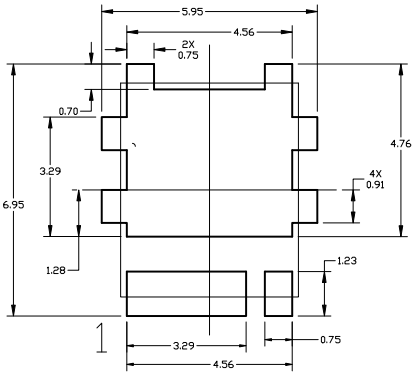
DETAIL B



BOTTOM VIEW

NOTES:
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 2009.
2. CONTROLLING DIMENSION: MILLIMETERS
3. DIMENSIONS D1 AND E1 DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.
4. THIS PACKAGE CONTAINS WETTABLE FLANK DESIGN FEATURES TO AID IN FILLET FORMATION ON THE LEADS DURING MOUNTING.

	MILLIMETERS		
DIM	MIN.	NOM.	MAX.
A	0.90	1.00	1.10
A1	0.00	---	0.05
b	0.33	0.41	0.51
c	0.23	0.28	0.33
D	5.00	5.15	5.30
D1	4.80	5.00	5.20
D2	3.90	4.10	4.30
E	6.00	6.15	6.30
E1	5.70	5.90	6.10
E2	3.55	3.75	3.95
e	1.27 BSC		
G	0.50	0.55	0.70
G1	0.26	0.36	0.46
k	1.10	1.25	1.40
L	0.50	0.60	0.70
L1	0.150 REF		
M	3.00	3.40	3.80
θ	0°	---	12°



RECOMMENDED
MOUNTING FOOTPRINT

* For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*

XXXX = Specific Device Code
A = Assembly Location
Y = Year
W = Work Week
ZZ = Assembly Lot

*This information is generic. Please refer to device data sheet for actual part marking. Pb−Free indicator, "G" or microdot "▪", may or may not be present. Some products may not follow the Generic Marking.

DOCUMENT NUMBER:	**98AON31027H**	Electronic versions are uncontrolled except when accessed directly from the Document Repository. Printed versions are uncontrolled except when stamped "CONTROLLED COPY" in red.
DESCRIPTION:	**DFNW5 5x6, FULL−CUT SO8FL WF**	**PAGE 1 OF 1**

ADDITIONAL INFORMATION

TECHNICAL PUBLICATIONS:
Technical Library: www.onsemi.com/design/resources/technical−documentation
onsemi Website: www.onsemi.com

ONLINE SUPPORT: www.onsemi.com/support
For additional information, please contact your local Sales Representative at www.onsemi.com/support/sales